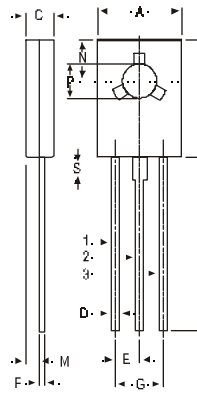
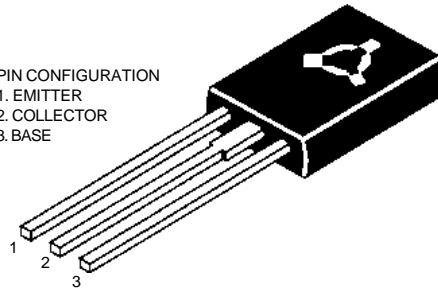




**MJE270**     *NPN PLASTIC POWER TRANSISTOR*  
**MJE271**     *PNP PLASTIC POWER TRANSISTOR*  
 Medium Power **Darlington** for Linear and Switching Applications

PIN CONFIGURATION  
 1. EMITTER  
 2. COLLECTOR  
 3. BASE



DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM

**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)	$V_{CBO}$	max.	100 V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	100 V
Collector current	$I_C$	max.	2.0 A
Total power dissipation up to $T_C = 25^\circ\text{C}$	$P_{tot}$	max.	15 W
Junction temperature	$T_j$	max.	150 °C
Collector-emitter saturation voltage $I_C = 20\text{ mA}; I_B = 0.2\text{ mA}$	$V_{CEsat}$	max.	2.0 V
D.C. current gain $I_C = 20\text{ mA}; V_{CE} = 3\text{ V}$	$h_{FE}$	min.	500

**RATINGS** (at  $T_A=25^\circ\text{C}$  unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)	$V_{CBO}$	max.	100 V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	100 V

## MJE270, MJE271

Emitter-base voltage (open collector)	$V_{EBO}$	max.	5.0 V
Collector current	$I_C$	max.	2.0 A
Collector current (peak)	$I_C$	max.	4.0 A
Base current	$I_B$	max.	0.1 A
Total power dissipation up to $T_C = 25^\circ\text{C}$	$P_{tot}$	max.	15 W
Derate above $25^\circ\text{C}$		max.	0.12 $\text{W}^\circ\text{C}$
Total power dissipation up to $T_A = 25^\circ\text{C}$	$P_{tot}$	max.	1.5 W
Derate above $25^\circ\text{C}$		max.	0.012 $\text{W}^\circ\text{C}$
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$
Storage temperature	$T_{stg}$		-65 to +150 $^\circ\text{C}$

### THERMAL RESISTANCE

From junction to case	$R_{th\ j-c}$	8.33 $^\circ\text{C/W}$
From junction to ambient	$R_{th\ j-a}$	83.3 $^\circ\text{C/W}$

### CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$  unless otherwise specified

Collector cutoff current			
$I_E = 0; V_{CB} = 100\text{ V}$	$I_{CBO}$	max.	0.3 mA
$I_B = 0; V_{CE} = 100\text{ V}$	$I_{CEO}$	max.	1.0 mA
Emitter cut-off current			
$I_C = 0; V_{EB} = 5\text{ V}$	$I_{EBO}$	max.	0.1 mA
Breakdown voltages			
$I_C = 10\text{ mA}; I_B = 0$	$V_{CEO(sus)}^*$	min.	100 V
$I_C = 1\text{ mA}; I_E = 0$	$V_{CB0}$	min.	100 V
$I_E = 1\text{ mA}; I_C = 0$	$V_{EBO}$	min.	5 V
Saturation voltages			
$I_C = 20\text{ mA}; I_B = 0.2\text{ mA}$	$V_{CEsat}^*$	max.	2.0 V
$I_C = 120\text{ mA}; I_B = 1.2\text{ mA}$	$V_{CEsat}^*$	max.	3.0 V
Base emitter on voltage			
$I_C = 120\text{ mA}; V_{CE} = 10\text{ V}$	$V_{BE(on)}^*$	max.	2.0 V
D.C. current gain			
$I_C = 20\text{ mA}; V_{CE} = 3\text{ V}$	$h_{FE}^*$	min.	500
$I_C = 120\text{ mA}; V_{CE} = 10\text{ V}$	$h_{FE}^*$	min.	1500
Transition frequency $f = 1\text{ MHz}$			
$I_C = 0.05\text{ A}; V_{CE} = 5\text{ V}$	$f_T(1)$	min.	6.0 MHz
Second Breakdown Collector Current with base Forward Biased			
$V_{CE} = 40\text{ V}; t = 1.0\text{ s};$ (non-repetitive)	$I_{S/b}$	min.	375 mA

(1)  $f_T = |h_{FE}| \cdot f_{test}$

\* Pulse test: pulse width  $\leq 300\ \mu\text{s}$ ; duty cycle  $\leq 2\%$ .